

TSM060N03CP

30V N-Channel Power MOSFET



Pin Definition:
 1. Gate
 2. Drain
 3. Source

Key Parameter Performance

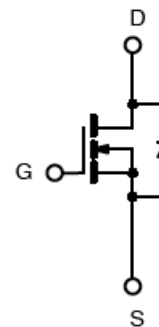
| Parameter | Value | Unit |
|--------------------|-----------------|------|
| V_{DS} | 30 | V |
| $R_{DS(on)}$ (max) | $V_{GS} = 10V$ | 6 |
| | $V_{GS} = 4.5V$ | 9 |
| Q_g | 11.1 | nC |

Ordering Information

| Ordering code | Package | Packing |
|-----------------|---------|--------------------|
| TSM060N03CP ROG | TO-252 | 2.5kpcs / 13" Reel |

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------|-------------------------------|------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_C=25^\circ C$ | 80 |
| | | $T_C=100^\circ C$ | 51 |
| Pulsed Drain Current ^(Note 1) | I_{DM} | 320 | A |
| Single Pulse Avalanche Energy ^(Note 2) | E_{AS} | 88 | mJ |
| Single Pulse Avalanche Current ^(Note 2) | I_{AS} | 42 | A |
| Total Power Dissipation | P_D | @ $T_C=25^\circ C$ | 54 |
| | | Derate above $T_C=25^\circ C$ | 0.43 |
| Operating Junction Temperature | T_J | 150 | $^\circ C$ |
| Storage Temperature Range | T_{STG} | -55 to +150 | $^\circ C$ |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|-----------------|-------|--------------|
| Thermal Resistance - Junction to Case | $R_{\theta JC}$ | 2.3 | $^\circ C/W$ |
| Thermal Resistance - Junction to Ambient | $R_{\theta JA}$ | 62 | $^\circ C/W$ |

Electrical Specifications (T_C=25°C unless otherwise noted)

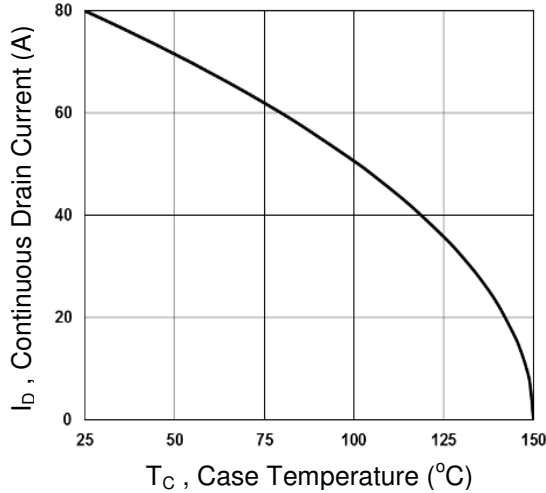
| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|--|---|---------------------|-----|------|------|------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{GS} = 0V, I _D = 250μA | BV _{DSS} | 30 | -- | -- | V |
| Drain-Source On-State Resistance | V _{GS} = 10V, I _D = 20A | R _{DS(ON)} | -- | 4.8 | 6 | mΩ |
| | V _{GS} = 4.5V, I _D = 10A | | -- | 6.5 | 9 | |
| Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | V _{GS(TH)} | 1 | 1.6 | 2.5 | V |
| Zero Gate Voltage Drain Current | V _{DS} = 30V, V _{GS} = 0V | I _{DSS} | -- | -- | 1 | μA |
| | V _{DS} = 24V, T _J = 125°C | | -- | -- | 10 | |
| Gate Body Leakage | V _{GS} = ±20V, V _{DS} = 0V | I _{GSS} | -- | -- | ±100 | nA |
| Forward Transconductance | V _{DS} = 10V, I _D = 10A | g _{fs} | -- | 18 | -- | S |
| Dynamic | | | | | | |
| Total Gate Charge ^(Note 3,4) | V _{DS} = 15V, I _D = 20A, V _{GS} = 4.5V | Q _g | -- | 11.1 | -- | nC |
| Gate-Source Charge ^(Note 3,4) | | Q _{gs} | -- | 1.85 | -- | |
| Gate-Drain Charge ^(Note 3,4) | | Q _{gd} | -- | 6.8 | -- | |
| Input Capacitance | V _{DS} = 25V, V _{GS} = 0V, f = 1MHz | C _{iss} | -- | 1160 | -- | pF |
| Output Capacitance | | C _{oss} | -- | 200 | -- | |
| Reverse Transfer Capacitance | | C _{rss} | -- | 180 | -- | |
| Gate Resistance | f = 1MHz | R _g | -- | 2.5 | -- | Ω |
| Switching | | | | | | |
| Turn-On Delay Time ^(Note 3,4) | V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω, I _D =-15A | t _{d(on)} | -- | 7.5 | -- | ns |
| Turn-On Rise Time ^(Note 3,4) | | t _r | -- | 14.5 | -- | |
| Turn-Off Delay Time ^(Note 3,4) | | t _{d(off)} | -- | 35.2 | -- | |
| Turn-Off Fall Time ^(Note 3,4) | | t _f | -- | 9.6 | -- | |
| Source-Drain Diode Ratings and Characteristic | | | | | | |
| Continuous Drain-Source Diode | | I _S | -- | -- | 80 | A |
| Pulse Drain-Source Diode | | I _{SM} | -- | -- | 320 | A |
| Diode-Source Forward Voltage | V _{GS} = 0V, I _S = 1A | V _{SD} | -- | -- | 1 | V |

Note:

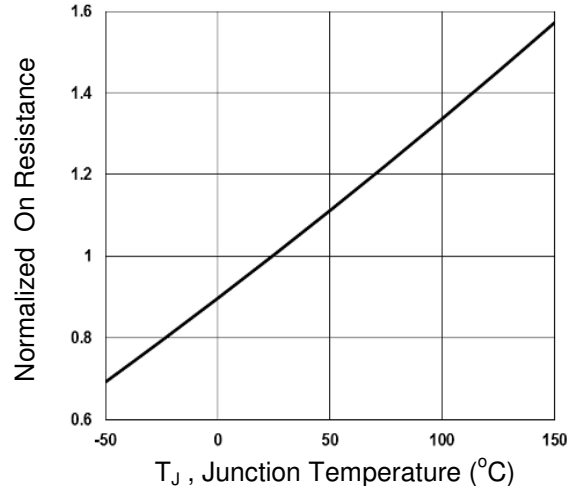
1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=42A, R_G=25Ω, Starting T_J=25°C
3. The data tested by pulsed, pulse width ≤300μs, duty cycle ≤2%
4. Essentially independent of operating temperature.

Electrical Characteristics Curve

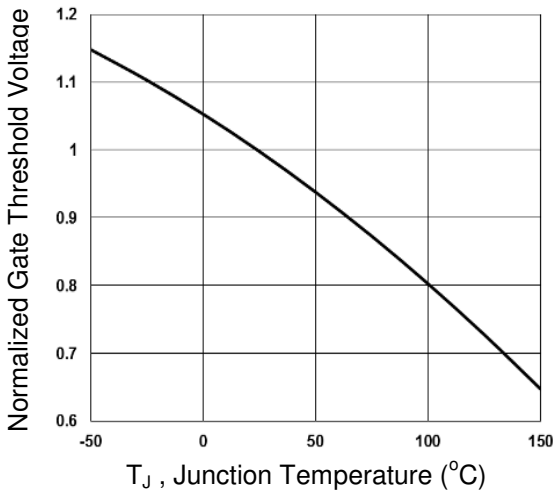
Continuous Drain Current vs. T_c



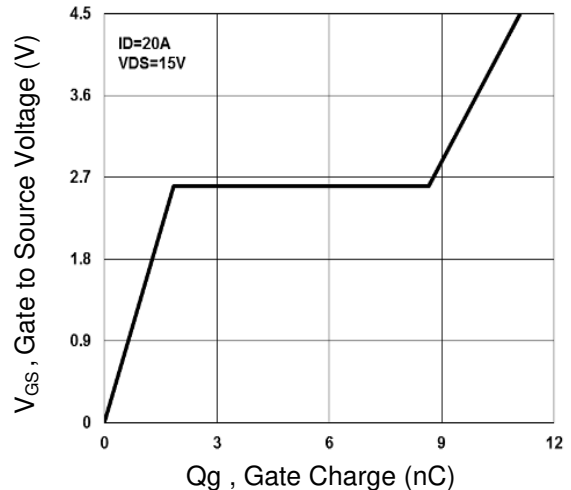
Normalized R_{DS(on)} vs. T_J



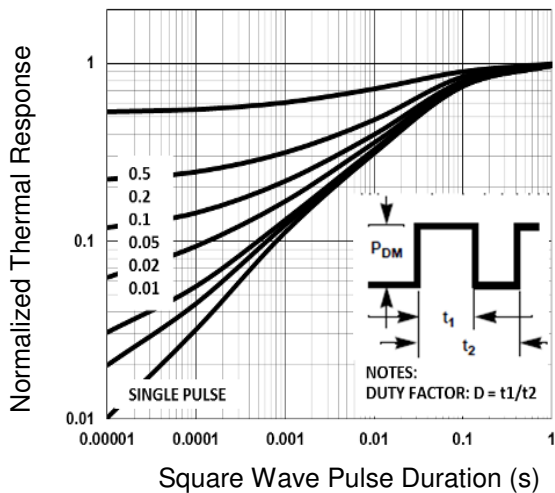
Normalized V_{th} vs. T_J



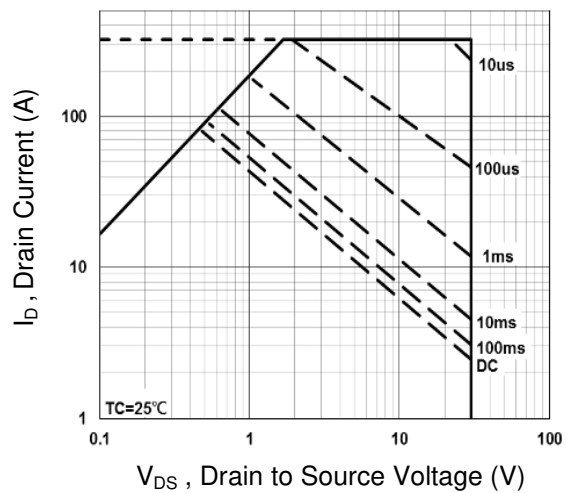
Gate Charge Waveform



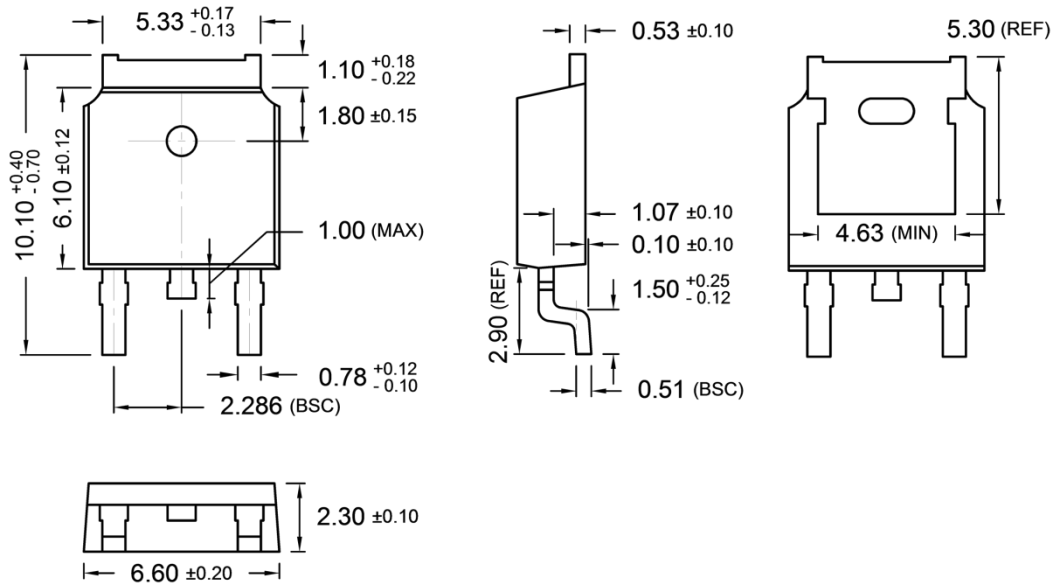
Normalized Transient Impedance



Maximum Safe Operation Area

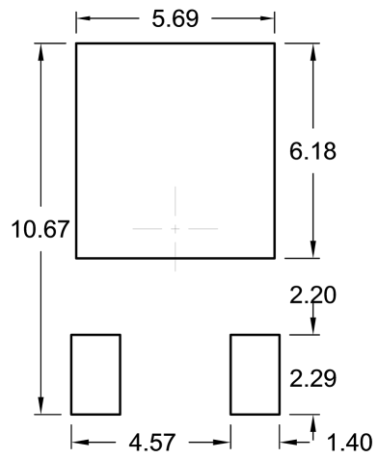


TO-252 Mechanical Drawing



Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



- Y** = Year Code
- M** = Month Code
- O** =Jan **P** =Feb **Q** =Mar **R** =Apr
- S** =May **T** =Jun **U** =Jul **V** =Aug
- W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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